

8. Method according to claim 1, wherein said dielectric coating film comprises silicon nitride including hydrogen, or amorphous silicon carbide including hydrogen.

9. Method according to claim 1, wherein after formation of said dielectric coating film, the method comprises annealing.

10. Method according to claim 9, wherein an annealing temperature is more than 50° C. higher than a deposition temperature of said dielectric coating film.

11. Method according to claim 1, wherein said dielectric coating film has a refraction index between 1.8-3.0.

12. Method according to claim 1, wherein said dielectric coating film, at least in use, functions as an anti-reflection coating film.

13. Method according to claim 1, wherein said dielectric coating film, at least in use, functions as an internal-reflection coating film.

14. A solar cell manufactured by a method according to claim 1.

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